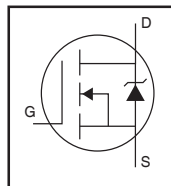


AUIRF3808

HEXFET® Power MOSFET

Features

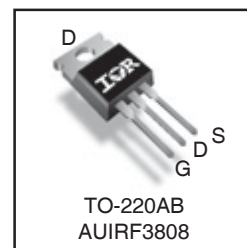
- Advanced Planar Technology
- Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified*



$V_{(BR)DSS}$	75V
$R_{DS(on)}$ typ.	5.9mΩ
	max
I_D	140A

Description

Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	140	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	97	
I_{DM}	Pulsed Drain Current ①	550	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	330	W
	Linear Derating Factor	2.2	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited)②	430	mJ
I_{AR}	Avalanche Current ①	82	A
E_{AR}	Repetitive Avalanche Energy ①⑥	See Fig. 12a, 12b, 15, 16	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑦	—	0.45	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

HEXFET® is a registered trademark of International Rectifier.

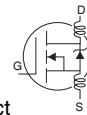
*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	75	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.086	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	5.9	7.0	mΩ	$V_{GS} = 10V, I_D = 82A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	100	—	—	S	$V_{DS} = 25V, I_D = 82A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 75V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 60V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

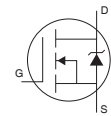
Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	150	220	nC	$I_D = 82A$ $V_{DS} = 60V$ $V_{GS} = 10V$ ④
Q_{gs}	Gate-to-Source Charge	—	31	47		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	50	76		
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 38V$ $I_D = 82A$ $R_G = 2.5\Omega$ $V_{GS} = 10V$ ④
t_r	Rise Time	—	140	—		
$t_{d(off)}$	Turn-Off Delay Time	—	68	—		
t_f	Fall Time	—	120	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	5310	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz$, See Fig. 5 $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$ $V_{GS} = 0V, V_{DS} = 60V, f = 1.0MHz$ $V_{GS} = 0V, V_{DS} = 0V$ to 60V
C_{oss}	Output Capacitance	—	890	—		
C_{rss}	Reverse Transfer Capacitance	—	130	—		
C_{oss}	Output Capacitance	—	6010	—		
C_{oss}	Output Capacitance	—	570	—		
$C_{oss\ eff.}$	Effective Output Capacitance ⑤	—	1140	—		



Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	140	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	550		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 82A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	93	140	ns	$T_J = 25^\circ\text{C}, I_F = 82A$
Q_{rr}	Reverse Recovery Charge	—	340	510	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.130mH$
 $R_G = 25\Omega, I_{AS} = 82A$. (See Figure 12).
- ③ $I_{SD} \leq 82A, di/dt \leq 310A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.

- ⑤ $C_{oss\ eff.}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑦ R_θ is measured at T_J of approximately 90°C .

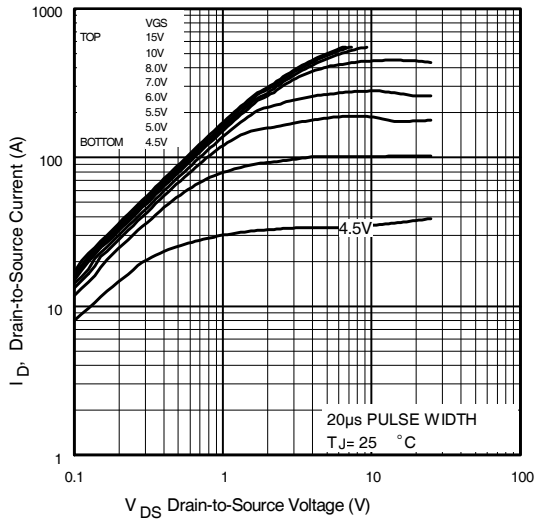


Fig 1. Typical Output Characteristics

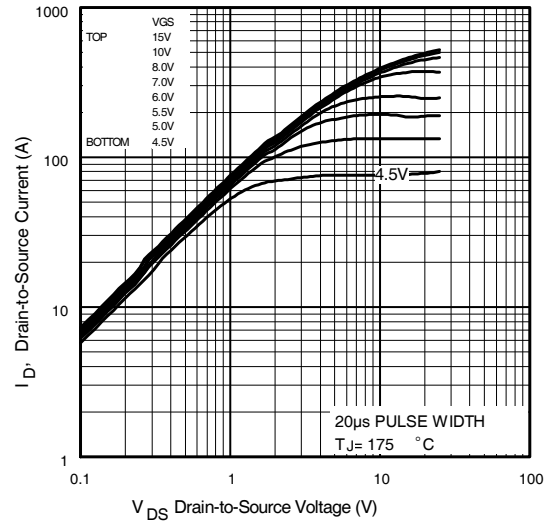


Fig 2. Typical Output Characteristics

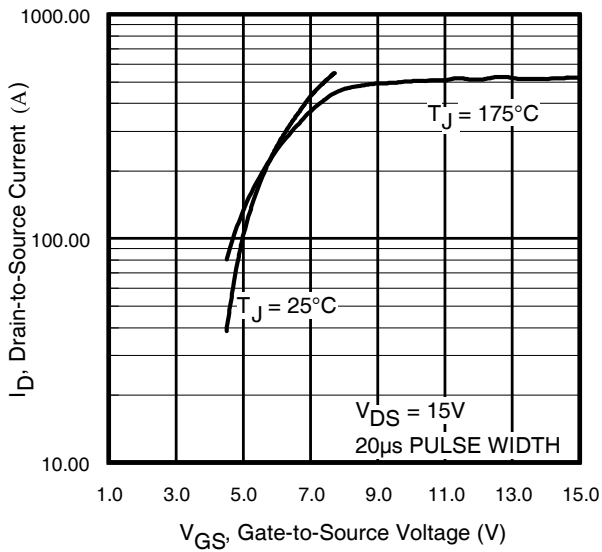


Fig 3. Typical Transfer Characteristics

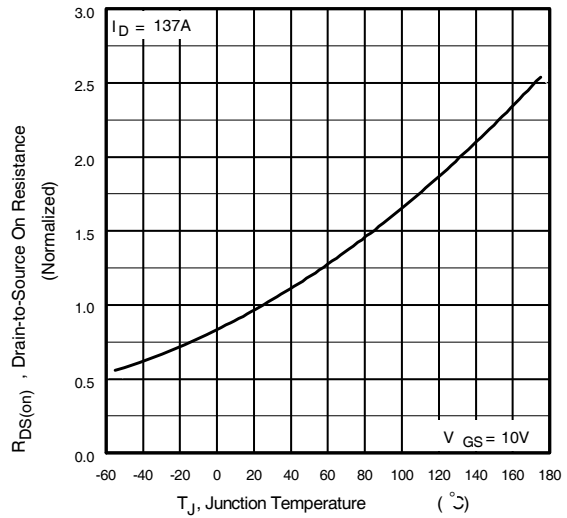


Fig 4. Normalized On-Resistance Vs. Temperature

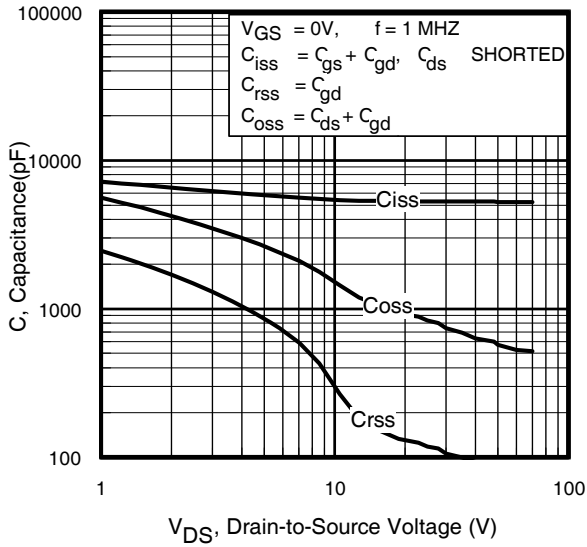


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

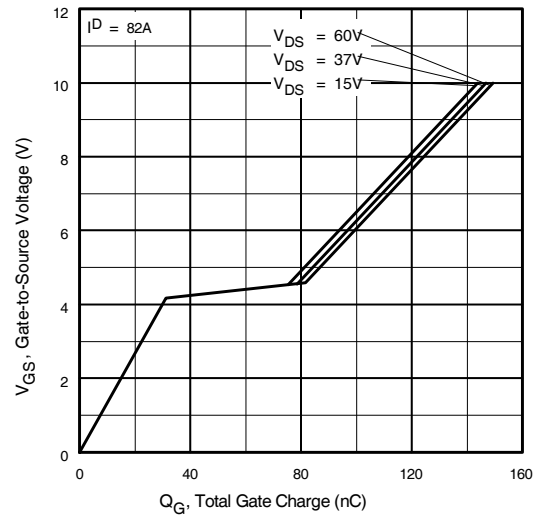


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

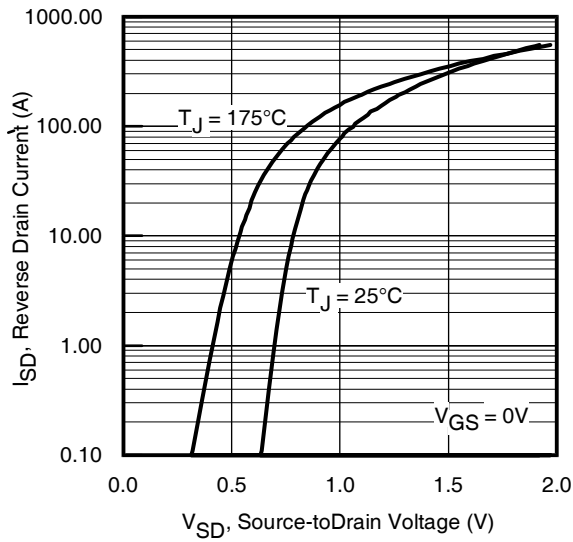


Fig 7. Typical Source-Drain Diode Forward Voltage

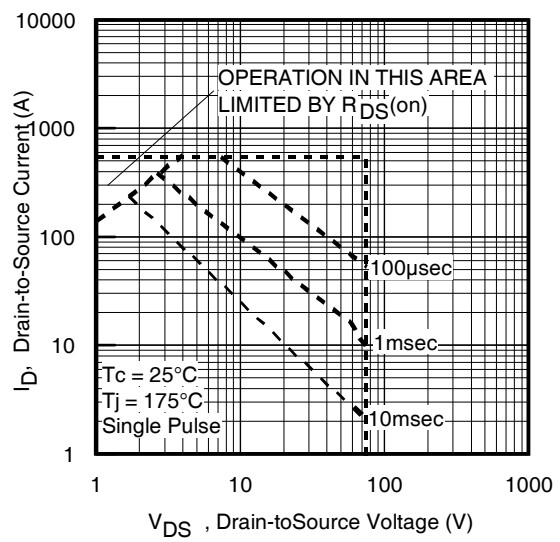


Fig 8. Maximum Safe Operating Area

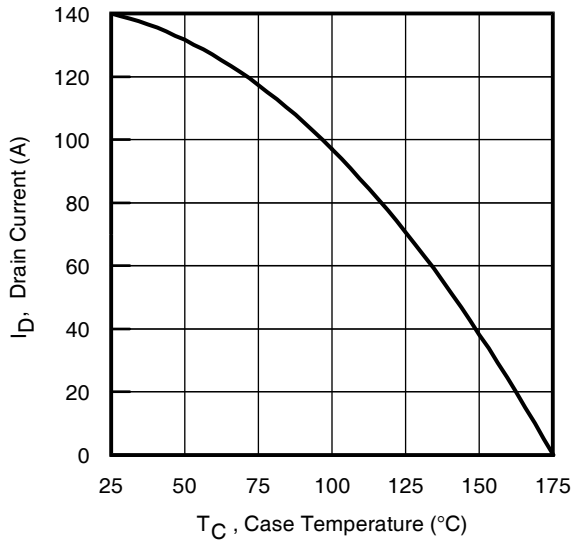


Fig 9. Maximum Drain Current Vs. Case Temperature

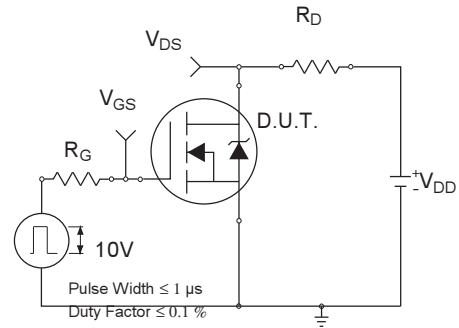


Fig 10a. Switching Time Test Circuit

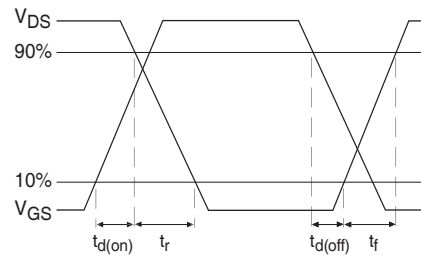


Fig 10b. Switching Time Waveforms

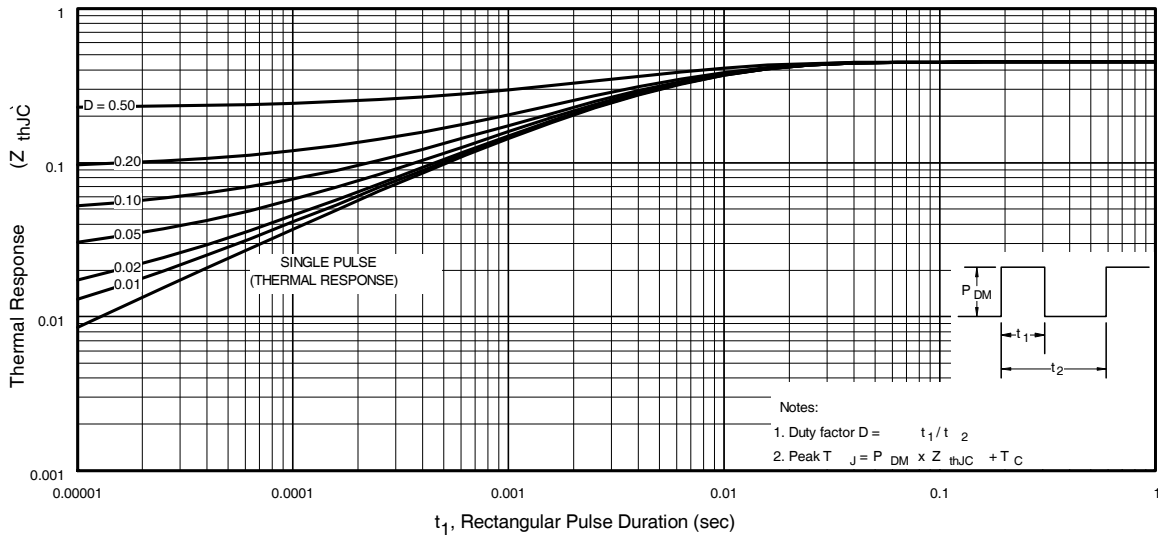


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

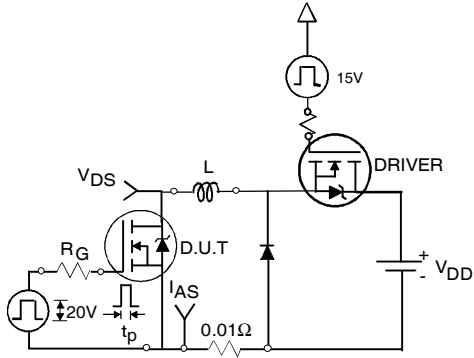


Fig 12a. Unclamped Inductive Test Circuit

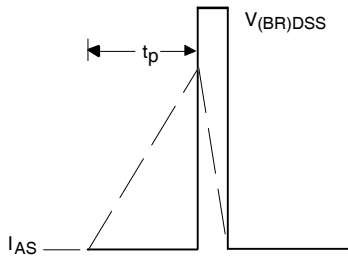


Fig 12b. Unclamped Inductive Waveforms

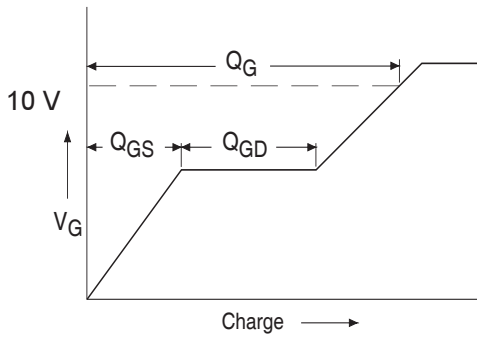


Fig 13a. Basic Gate Charge Waveform

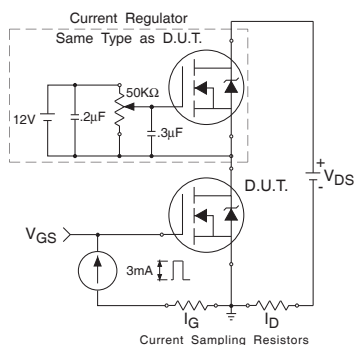


Fig 13b. Gate Charge Test Circuit

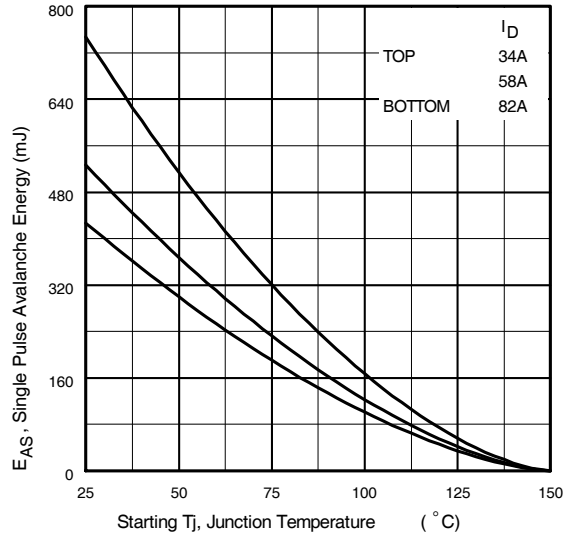


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

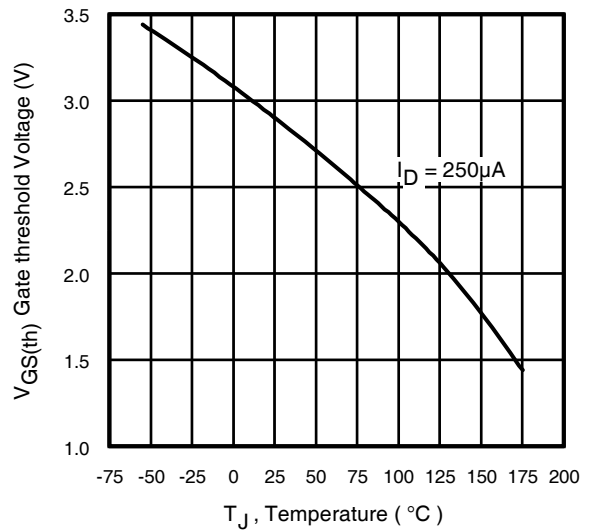


Fig 14. Threshold Voltage Vs. Temperature

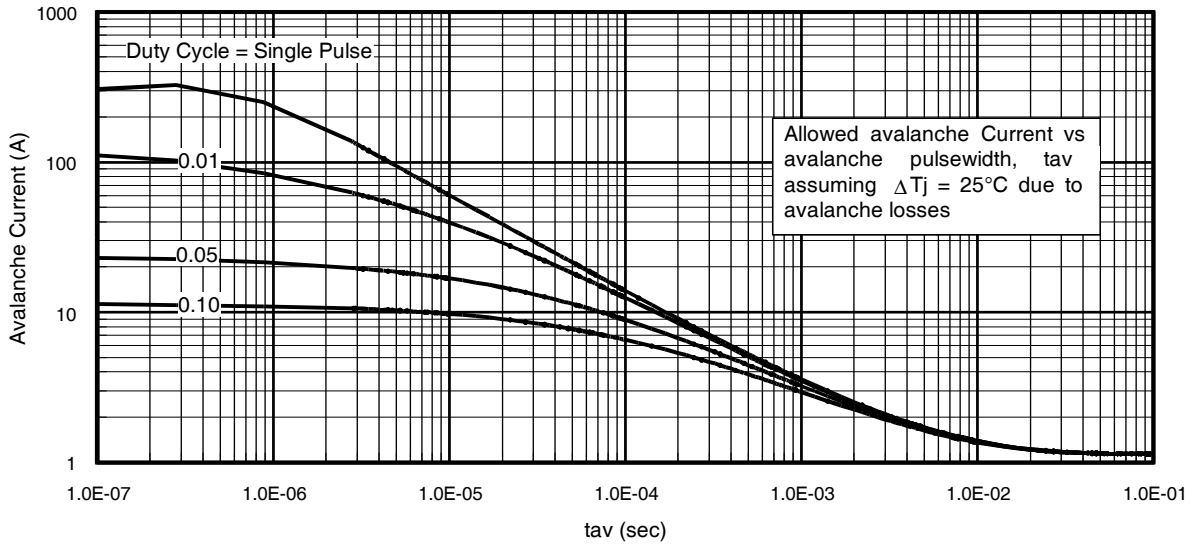
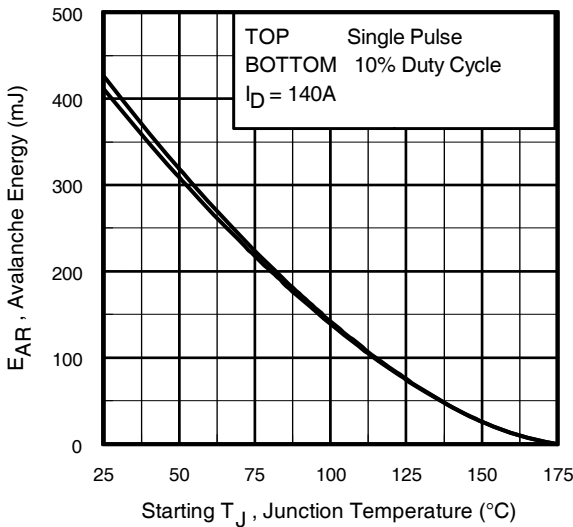


Fig 15. Typical Avalanche Current Vs.Pulsewidth



Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

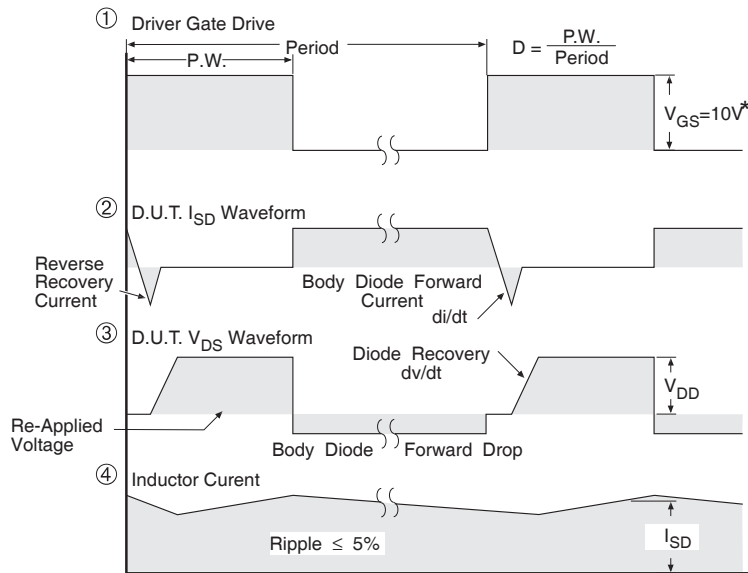
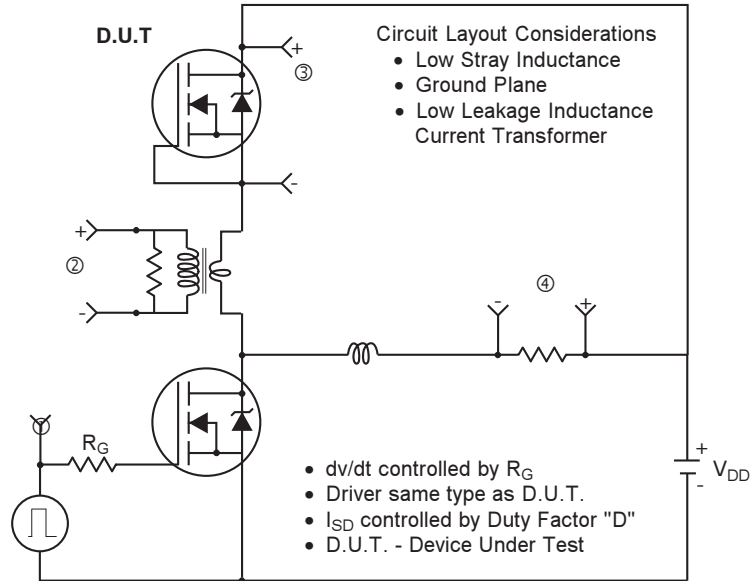
$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 16. Maximum Avalanche Energy Vs. Temperature

Peak Diode Recovery dv/dt Test Circuit

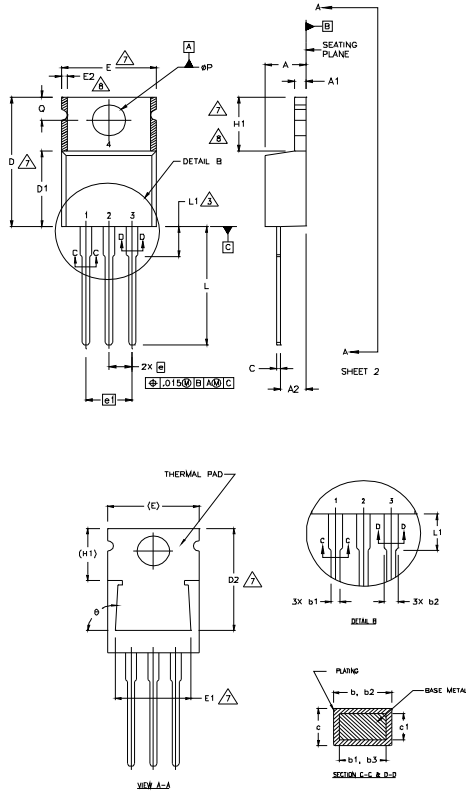


* $V_{GS} = 5V$ for Logic Level Devices

Fig 17. For N-channel HEXFET® power MOSFETs

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
- 6 CONTROLLING DIMENSION : INCHES.
- 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs - CoPACKS

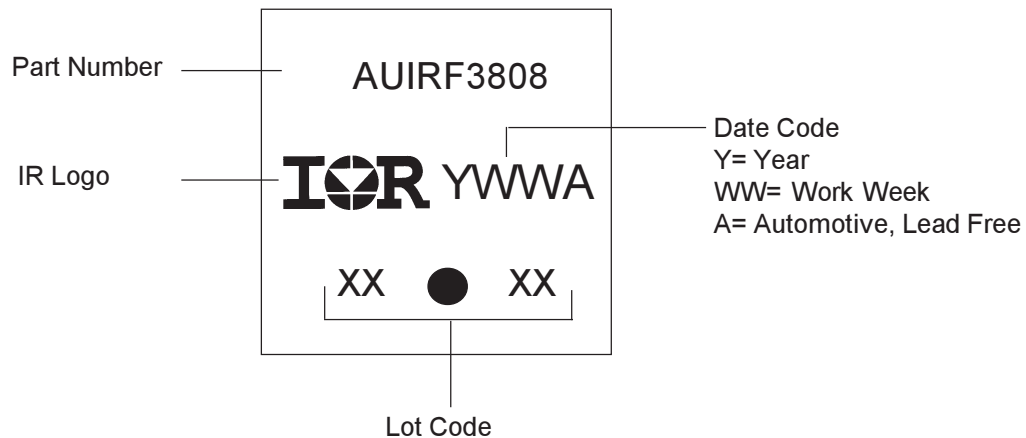
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	18.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90°-93°		90°-93°		

TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF3808	TO-220	Tube	50	AUIRF3808

IMPORTANT NOTICE

Unless specifically designated for the automotive market, International Rectifier Corporation and its subsidiaries (IR) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or services without notice. Part numbers designated with the "AU" prefix follow automotive industry and / or customer specific requirements with regards to product discontinuance and process change notification. All products are sold subject to IR's terms and conditions of sale supplied at the time of order acknowledgment.

IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR's standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

IR assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using IR components. To minimize the risks with customer products and applications, customers should provide adequate design and operating safeguards.

Reproduction of IR information in IR data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alterations is an unfair and deceptive business practice. IR is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of IR products or serviced with statements different from or beyond the parameters stated by IR for that product or service voids all express and any implied warranties for the associated IR product or service and is an unfair and deceptive business practice. IR is not responsible or liable for any such statements.

IR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or in other applications intended to support or sustain life, or in any other application in which the failure of the IR product could create a situation where personal injury or death may occur. Should Buyer purchase or use IR products for any such unintended or unauthorized application, Buyer shall indemnify and hold International Rectifier and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that IR was negligent regarding the design or manufacture of the product.

Only products certified as military grade by the Defense Logistics Agency (DLA) of the US Department of Defense, are designed and manufactured to meet DLA military specifications required by certain military, aerospace or other applications. Buyers acknowledge and agree that any use of IR products not certified by DLA as military-grade, in applications requiring military grade products, is solely at the Buyer's own risk and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements.

For technical support, please contact IR's Technical Assistance Center
<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:
101 N. Sepulveda Blvd., El Segundo, California 90245
Tel: (310) 252-7105